

1 **Supplementary Material - 3D-printed components for quantum devices**

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Supplementary Note 1 - Device model

11 A simple idealized comparison of a three-dimensional
 12 (3D) versus two-dimensional (2D) scenario of generating
 13 a quadrupole field demonstrates the key principles behind
 14 beneficial power consumption. We consider a planarised
 15 conductor configuration forming a quadrupole field with
 16 an out-of-plane zero formed by multiple in-plane cur-
 17 rents, whose fields compensate each other at the zero po-
 18 sition. As all these fields necessarily drop monotonically in
 19 magnitude with distance from the plane, the field gradi-
 20 ents will also at least partially compensate each other
 21 at the field zero. This gradient compensation needs to
 22 be minimised in order to obtain a power-efficient planar
 23 solution. In contrast in 3D the currents generating the
 24 fields that cancel at the trap center position of a device
 25 can be formed in such a way that the gradients produced
 26 by them add, rather than subtract as in planar imple-
 27 mentation.

28 As a simple model illustrating the 2D vs 3D differ-
 29 ence, we choose two infinitesimally thin current loops in
 30 the anti-Helmholtz configuration (two parallel loops with
 31 equal radius R carrying equal currents I are placed at
 32 a distance $d = R$ from each other) and compare them
 33 to two in-plane concentric current loops (Supplementary
 34 Figure 1). The in-plane loops have radii R_1 and R_2 and
 35 carry currents I_1 and I_2 , respectively. The 3D configura-
 36 tion field zero occurs at a distance $R/2$ from either loop.
 37 Consequently, the planar configuration parameters are
 38 chosen such that a field zero forms at $R/2$ from the cur-
 39 rent plane in that case. We further impose equal power
 40 consumption in both configurations which is obtained
 41 when $R_1 I_1^2 + R_2 I_2^2 = 2RI^2$. Finally, we require the
 42 field curvature to vanish at the field zero, so that in ap-
 43 proximation of the ideal quadrupole field the field varies
 44 only linearly at this center position. Note that without
 45 loss of generality it is sufficient to only consider the field
 46 along the loops' symmetry axis z , where the field is al-
 47 ways oriented along z . We find that under the above con-
 48 straints the maximal gradient is achieved in the planar
 49 configuration when $R_1 = 1.14R$ and $R_2 = 2.51R$ with
 50 the currents $I_1 = 0.46I$ and $I_2 = -0.84I$. Even in this
 51 optimal configuration, the gradient is reduced by a factor
 52 larger than 7 with respect to the 3D anti-Helmholtz con-
 53 figuration. Calculated field configurations are shown in
 54 Supplementary Figure 1(a) for a 3D structure and (b) for
 55 a planar structure. Supplementary Figure 1(c) displays
 56 the corresponding fields along the symmetry axis of the
 57 loops. To match the gradient obtained in the 3D config-
 58 uration with the 2D configuration requires a more than
 59 50-fold increase of power consumption.

60 Now let us examine the relationship between device
 61 size and power consumption. Again, for the 3D case, the
 62 idealised anti-Helmholtz configuration may serve as an
 63 illustration of a scaling law that is extendible to more

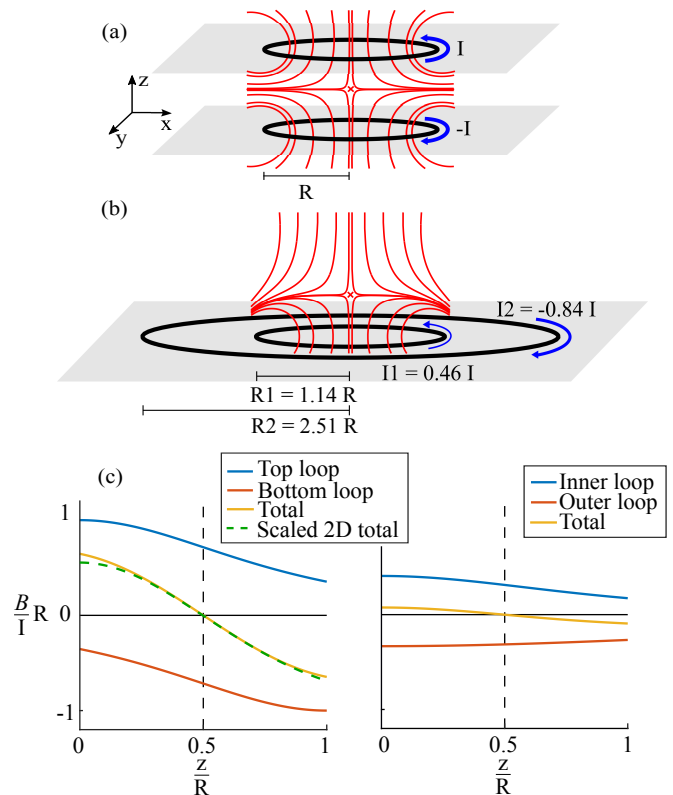


FIG. 1. Comparison of two quadrupole field generating structures whereby two current loops are placed in two parallel planes (3D) or a single plane (2D). Streamline plots show the field produced from the 3D system (a) and 2D system (b). (c) Magnetic field strength along the symmetry axis z of the current loops (due to symmetry radial fields vanish). The field of one loop (blue) is compensated by the other (red) in both configurations at the same zero-field position (red cross). At equal power consumption, the total field gradient (yellow) for the 3D system is stronger than that in the 2D case by a factor of 7.37. To reach the same gradient with the planar 2D assembly, the current needs to be scaled up by the same factor (dashed green line). This corresponds to an increased power dissipation by a factor of 54.3.

64 general magnetic field generating structures. In the anti-
 65 Helmholtz configuration, as in other configurations e.g.
 66 for magnetic traps of various shapes, the key parameter
 67 is the generated field gradient at the field zero (field min-
 68 imum). As the field of a single current loop at the po-
 69 sition of the quadrupole field zero ($z = R/2$) scales as
 70 $\sim 1/R$, the gradient at that position scales as $\sim 1/R^2$.
 71 Conversely, in order to maintain a constant gradient, the
 72 required current scales as $\sim R^2$. If the conductor cross
 73 section is assumed to scale with size of the device, the
 74 resistance Z of the structure increases with the length
 75 of the current loop ($\sim R$) and drops as $\sim 1/R^2$ with
 76 the cross section, such that the Ohmic power dissipation
 77 scales as $P = ZI^2 \sim R^3$. This signifies that power con-
 78 sumption will drop cubically as we scale down the device
 79 with a characteristic radius.

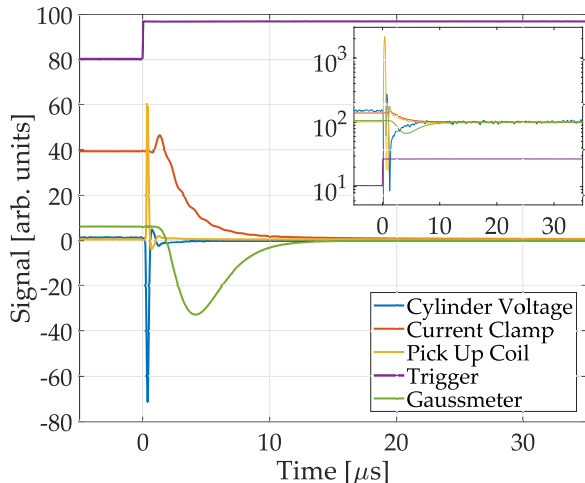


FIG. 2. Magnetic field decay measurement. The plot shows the characteristics of the switch-off process for the cylinder, using a current of 15 A. The voltage across the device itself (blue trace) is displayed, along with the current flowing via a current clamp (red), after sending a trigger (purple) to open an IGBT. Also shown is the voltage induced in a pick-up coil due to changes in the magnetic field (yellow), along with the signal from a Hall effect Gaussmeter (green). After an initial transient period, the Hall probe signal decays to below 10% of its initial value within $(13.0 \pm 2.3) \mu\text{s}$, after which time all signals settle to their steady state background readings. The inset depicts the same data set on a semi-log plot to emphasise the similar decay times of all measured signals.

80 Supplementary Note 2 - Field Decay Measurement

81 It is important to investigate the decay of the magnetic
82 field after switching off the trap as this can limit the
83 experimental cycle length in typical cold atom devices.

84 To characterise this switching process, the voltage
85 across the cylinder was measured along with the cur-
86 rent flowing through it using a current clamp (Chauvin
87 Arnoux P01120043A), as a function of time after opening
88 an insulated gate bipolar transistor (IGBT). In addition,
89 the magnetic field inside the cylinder during the switch-
90 ing was measured using a Hall effect Gaussmeter (Hirst
91 GM08) and its derivative with a small single-turn pick-
92 up coil. Both the Hall probe and the pick-coil were ori-
93 ented along the strong eigenaxis of the quadrupole field,
94 at the position of largest field. The results are shown

95 by the signal traces in Supplementary Figure 2, obtained
96 for a current of 15 A, corresponding to a magnetic field
97 of $(6.2 \pm 0.6) \text{ G}$ at the position of the Hall probe.

98 Shortly after opening the IGBT, a large flyback voltage
99 develops across the cylinder, as expected when switching
100 a current through an inductive load. Some oscillatory
101 behaviour can also be seen, arising due to contact res-
102 istances and small parasitic capacitance and inductance
103 within the circuit, which are non-negligible in compar-
104 ison to the impedance characteristics of the cylinder it-
105 self. Following the initial transient period of the switch-
106 ing process, the magnetic field measured with the Hall
107 probe is seen to decay below 10% of its initial value
108 within $(13.0 \pm 2.3) \mu\text{s}$.

109 Finally, in order to determine the inductance, L , of
110 the cylinder the resonant frequencies, $f_{\text{res}}(C)$, of a par-
111 allel LC circuit for various known capacitances, C , were
112 measured with a network analyser (Mini Radio Solutions
113 miniVNA). Supplementary Figure 3 shows a plot of f_{res}^2
114 against $1/C$, and using the relation $f_{\text{res}}^2 = 1/(4\pi^2 LC)$,
115 a value for the inductance of $(0.49 \pm 0.05) \mu\text{H}$ is extracted
116 from the gradient of the linear fit.

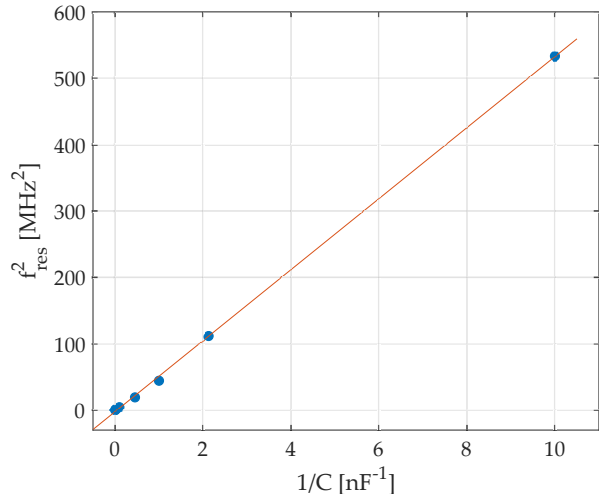


FIG. 3. Cylinder inductance measurement. A plot showing the resonant frequencies, $f_{\text{res}}(C)$ of a parallel LC circuit for various known capacitances, from which an inductance of $(0.49 \pm 0.05) \mu\text{H}$ is extracted from the linear fit, as described in the text.